Product Preview

Digital MEMS Microphone Controller including Pre-amplifier and Sigma Delta Modulator and Charge Pump



ON Semiconductor®

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Description

The LC706206CA is a MOS LSI which integrates digital MEMS microphone controller function. It supplies bias voltage to external MEMS sensor and accepts analog sound signal, outputs PDM (Pulse Density Modulation) data stream.

The LC706206CA includes LDO, pre-amplifier, ADC (Analog-to Digital Converter) and charge-pump. The charge-pump generates bias voltage which is needed by the MEMS sensor. The pre-amplifier amplifies analog sound signal from the MEMS sensor and drives ADC to obtain PDM data stream.

The LC706206CA features an integrated LDO and is powered from the system supply rails up to 3.6 V, with low current consumption of 550 $\mu A(typ)$ at normal operation mode (Fclk = 2.4 MHz). It also has the low power mode (Fclk = 750 kHz).

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

ORDERING INFORMATION

| Device | Package | Shipping (Qty / Packing) |
|------------|-----------------|--------------------------|
| LC706206CA | Wafer (Pb-Free) | 1 / Wafer Carrier |

Features

- Optimized to be combined with a MEMS Sensor with 11 V Bias Voltage and -39 dBV @ 94 dBSPL Sensitivity
- Pulse Density Modulation (PDM) Output
- Standard 5-Wire Digital Interface
- 11.0 V Charge-pump Output for MEMS Sensor Bias
- +13 dB Gain (Transfer Function)
- Low Noise –90 dBFS Output makes total SNR up to 63 dB
- Low Current Consumption 550 μA(typ) at Fclk = 2.4 MHz
- Low Power Mode at Fclk = 750 kHz in which the Current Consumption 300 μA(typ)
- This is a Pb-Free Device

Applications

- Digital MEMS Microphone
- Personal Computer
- Tablet Computer
- Mobile Handset
- Headset Accessories

Block Diagram

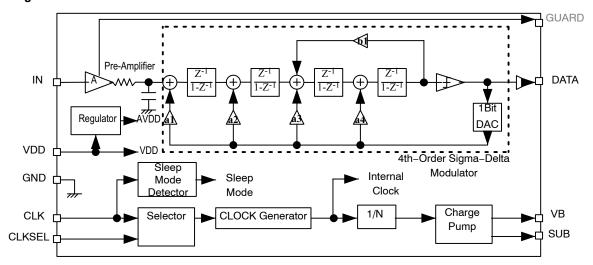
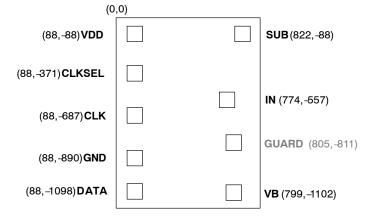


Figure 1. Block Diagram

Pad Coordinate Pad Size



80 μm (Jacket Open Area)

Figure 3. Pad Size

Figure 2. Pad Coordinate

Wafer Outline

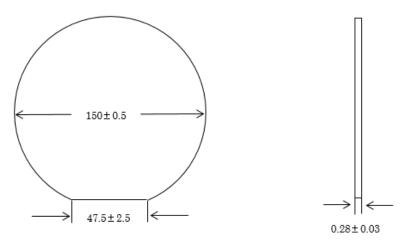


Figure 4. Wafer Outline

Table 1. ABSOLUTE MAXIMUM RATINGS at T_a = 25°C, GND = 0 V

| Parameter | Symbol | Pin Name | Min | Max | Unit |
|------------------------------|----------------------|----------------|------|-----------------------|------|
| Maximum power supply voltage | V _{DD} max | VDD | -0.3 | +4.0 | V |
| Maximum input voltage | V _{CLK} max | CLOCK, LR, ADJ | -0.3 | V _{DD} + 0.3 | V |
| | V _{IN} max | IN | -0.3 | V _{DD} + 0.3 | V |
| Maximum output voltage | V _O max | DATA | -0.3 | V _{DD} + 0.3 | V |
| Operating temperature range | Та | | -30 | 70 | °C |
| Storage temperature range | Tstg | | -40 | 85 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 2. CIRCUIT PARAMETERS (Note 1)

| Parameter | Symbol | Pin Name | Test Condition | Min | Тур | Max | Unit |
|--------------------------|-----------------|----------|----------------|-----|-----|-----|------|
| Input capacitance of die | C _{IN} | IN | | | 0.4 | | pF |

^{1.} IN-Pin has a limited protection against ESD. Value of IN-Pin is proven by design.

 $\textbf{Table 3. DC ELECTRICAL CHARACTERISTICS RATING} \ \ \text{at } \ T_{a} = 25^{\circ}\text{C}, \ V_{DD} = 1.8 \ \text{V}, \ \text{GND} = 0 \ \text{V}, \ \text{Fclk} = 2.4 \ \text{MHz}, \ \text{Fduty} = 50\%$

| Parameter | Symbol | Pin Name | Condition | Min | Тур | Max | Unit |
|-------------------------|-----------------|----------------------|---|------------------------|------|----------------------|------|
| Power supply voltage | V _{DD} | VDD | | 1.64 | 1.8 | 3.6 | V |
| Current consumption 1 | IDD1 | VDD | V _{DD} = 1.8 V Fclk = 3.0 MHz | | 550 | | μΑ |
| Current consumption 2 | IDD2 | VDD | V _{DD} = 1.8 V Fclk = 750 kHz | | 300 | | μΑ |
| Standby Current | ISTBY | VDD | V _{DD} = 3.3 V Fclk < 1 kHz | | | 1 | μΑ |
| Input/Output LOW level | Viol | CLK, DATA, CLKSEL | DATA : lol = 0.5 mA | | | $0.35 \times V_{DD}$ | V |
| Input/Output HIGH level | Vioh | CLK, DATA, CLKSEL | DATA : loh = -0.5 mA | 0.65 × V _{DD} | | | V |
| Charge pump voltage | Vbias | VB/SUB | V _{DD} = 3.3 V | 9.66 | 10.5 | 11.34 | ٧ |
| Load Capacitance | Cload | DATA | V _{DD} = 1.64 V | | | 200 | pF |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Table 4. AC ELECTRICAL CHARACTERISTICS DESIGN

at T_a = 25°C, V_{DD} = 1.8 V, GND = 0 V, Signal Frequency = 1 kHz, Measurement frequency = 100 Hz to 20 kHz, Fclk = 2.4 MHz, Fduty = 50%, Input capacitor = 2.5 pF, Bypass capacitor = 0.1 μ F (V_{DD} – GND)

| Parameter | Symbol | Pin Name | Condition | Min | Тур | Max | Unit |
|---------------------------------------|---------------------|----------|--|------|-------|------|--------------|
| Clock Frequency (Normal Operation) | Fclk | CLK | | 0.6 | 2.4 | 3.3 | MHz |
| Clock Frequency (Sleep Mode) | Fclk_SL | CLK | | | | 1 | kHz |
| Clock Duty (Note 2) | Fduty | CLK | | 40 | | 60 | % |
| Over Sampling Ratio | OSR | | | | 50 | | |
| Maximum Input Voltage | Vin (Note 2) | IN | 0 dBFS (= 122 dBSPL) | | 223.8 | | mVrms |
| THD / THD+N | THD+N_0 | DATA | Vout = -2 dBFS (= 120 dBSPL) 1 kHz Sin-Wave | | | 5 | % (THD) |
| | THD+N_1 | DATA | Vout = -5 dBFS (= 117 dBSPL) 1 kHz Sin-Wave | | | 3 | % (THD+N) |
| | THD+N_2 | DATA | Vout = -12 dBFS (= 110 dBSPL) 1 kHz Sin-Wave | | | 1 | % (THD+N) |
| | THD+N_3 | DATA | Vout = -28 dBFS (= 94 dBSPL) 1 kHz Sin-Wave | | | 0.5 | % (THD+N) |
| Digital Noise Floor | DNF_1 | DATA | Fclk = 2.4 MHz A-weighted | | -90.0 | | dBFS |
| | DNF_2 | DATA | Fclk = 750 kHz A-weighted | | -89.0 | | dBFS |
| Transfer Function (Note 3) | TF1 | DATA | | | 13.0 | | dB |
| Transfer Function vs Fclk | TF_Fclk (Note 2) | DATA | | -0.1 | | +0.1 | dB |
| Power Supply Rejection | PSR (Note 2) | DATA | 20 Hz to 20 kHz, 100 mVp-p sine wave | | | -80 | dBFS |
| Wake Up Time (Note 2) | WUT_1 | DATA | -0.5 dBFS to final value | | | 20 | ms |
| | WUT_2 | DATA | -0.2 dBFS to final value | | | 50 | ms |
| Fall Asleep Time (Note 2) | FAT | DATA | Fclk = 1 kHz | | | 10 | ms |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{2.} Reference data: No measurement.

^{3.} Each product has been designed with performance of ±0.5 dB tolerance for transfer function however it's not measured in outgoing inspection.

Table 5. PIN DESCRIPTIONS

| No. | Pin Name | Function | I/O | Pin Conditions |
|-----|----------|--|--------|----------------|
| _ | GND | Ground | - | - |
| _ | VDD | Power Supply | _ | - |
| _ | GUARD | Connect to GUARD of MEMS | - | - |
| _ | SUB | Connect to SUB of MEMS | - | - |
| _ | DATA | PDM Data Output | Output | |
| - | CLKSEL | CLK Select signal input Case 1: When CLKSEL is LOW, PDM data is outputted in sync with negative edge of CLK. Case 2: When CLKSEL is HIGH, PDM data is outputted in sync with positive edge of CLK. | Input | |
| _ | CLK | Clock input | Input | |
| _ | VB | Charge Pump Voltage Output | Output | - |
| _ | IN | Audio signal input | Input | |

Table 6. SWITCHING CHARACTERISTICS

at T_a = 25°C, V_{DD} = 1.8 V, GND = 0 V, Fclk = 2.4 MHz, Fduty = 50%

Case 1: CLKSEL = LOW

| Parameter | Symbol | Pin Name | Condition | Min | Тур | Max | Unit |
|-------------------|--------|----------|-------------------------------|-----|-----|-----|------|
| Clock Rise Time | Tcr | CLK | | | | 10 | ns |
| Clock Fall Time | Tcf | CLK | | | | 10 | ns |
| Output Data Delay | Tpd_I | DATA | CL = 13 pF, RL = 1 M Ω | 18 | | 60 | ns |
| Output Hi-Z Delay | Tpzd_l | DATA | CL = 13 pF, RL = 1 M Ω | 0 | | 16 | ns |

NOTE: $Tpd_I > Tpzd_I$

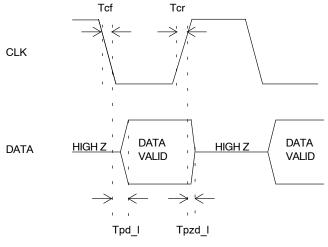


Figure 5.

Table 7. SWITCHING CHARACTERISTICS (Reference data: No measurement)

at $T_a = 25$ °C, $V_{DD} = 1.8$ V, GND = 0 V, Fclk = 2.4 MHz, Fduty = 50%

Case 2: CLKSEL = HIGH

| Parameter | Symbol | Pin Name | Condition | Min | Тур | Max | Unit |
|-------------------|--------|----------|-------------------------------|-----|-----|-----|------|
| Clock Rise Time | Tcr | CLK | | | | 10 | ns |
| Clock Fall Time | Tcf | CLK | | | | 10 | ns |
| Output Data Delay | Tpd_h | DATA | CL = 13 pF, RL = 1 M Ω | 18 | | 60 | ns |
| Output Hi-Z Delay | Tpzd_h | DATA | CL = 13 pF, RL = 1 M Ω | 0 | | 16 | ns |

NOTE: Tpd_h > Tpzd_h

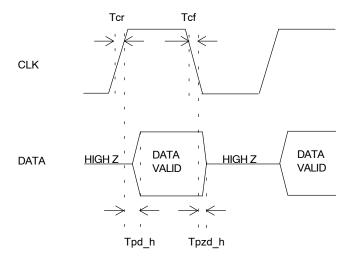


Figure 6.

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